

## LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:  
a substrate of a first conductivity type;  
an epitaxial layer of said first conductivity type formed over a major surface of said substrate;  
a plurality of stripes of a second conductivity type only being formed in a top surface of said epitaxial layer, each of said ~~regions~~ stripes of said second conductivity type extending to a first depth and laterally spaced from another ~~region~~ stripe of said second conductivity type by a distance selected so that said device exhibits the same reverse avalanche energy absorption characteristics as a Fast Recovery Epitaxial Diode having a diffusion of a depth higher than said first depth; and  
a schottky contact layer in contact with said plurality of spaced ~~regions~~ stripes of said second conductivity type and regions of said first conductivity type disposed between said spaced ~~regions~~ stripes of said second conductivity type.
- 2.-3. (Canceled).
4. (Previously Presented) A semiconductor device according to claim 1, wherein said stripes of said second conductivity type are five microns deep.
5. (Original) A semiconductor device according to claim 1, wherein said schottky contact layer is comprised of aluminum.
6. (Previously Presented) A semiconductor device according to claim 1, wherein said distance between a stripe of said second conductivity type and another stripe of said second conductivity type is eight microns.

7. (Previously Presented) A semiconductor device according to claim 1, wherein said distance between a stripe of said second conductivity type and another stripe of said second conductivity type is twelve microns.

8. (Previously Presented) A semiconductor device according to claim 1, wherein said distance between a stripe of said second conductivity type and another stripe of said second conductivity type is nineteen microns.

9. (Previously Presented) A semiconductor device according to claim 1, wherein said distance between said stripes of said second conductivity type is between eight microns and nineteen microns.

10. (Previously Presented) A semiconductor device according to claim 1, wherein said distance between a stripe of said second conductivity type and another stripe of said second conductivity type is no more than nineteen microns.

11. (Original) A semiconductor device according to claim 1, further comprising a back contact layer disposed over a second major surface of said substrate opposing said first major surface.

12. (Withdrawn) A method for manufacturing a semiconductor device comprising:  
forming a plurality of regions of one conductivity type in a semiconductive body of another conductivity, each of said regions extending to a first depth;

spacing each of said regions of one conductivity type from another region of one conductivity type a distance selected so that said device exhibits the same reverse avalanche energy absorption characteristics as a Fast Recovery Epitaxial Diode having a diffusion of a depth higher than said first depth; and

forming a schottky contact layer over said semiconductive body, wherein said schottky contact layer is in contact with said plurality of spaced regions of said one conductivity and

regions of said another conductivity type disposed between said spaced regions of said one conductivity.

13. (Withdrawn) A method according to claim 12, wherein said schottky contact layer is comprised of aluminum.

14. (Withdrawn) A method according to claim 12, wherein said distance between a region of said one conductivity type and another region of said one conductivity type is eight microns.

15. (Withdrawn) A method according to claim 12, wherein said distance between a region of said one conductivity type and another region of said one conductivity type is twelve microns.

16. (Withdrawn) A method according to claim 12, wherein said distance between a region of said one conductivity type and another region of said one conductivity type is twelve microns.

17. (Withdrawn) A method according to claim 12, wherein said distance between a region of said one conductivity type and another region of said one conductivity type is between eight microns and nineteen microns.

18. (Withdrawn) A method according to claim 12, wherein said distance between a region of said one conductivity type and another region of said one conductivity type is no more than nineteen microns.

19. (Withdrawn) A method according to claim 12, further comprising a back contact layer disposed over a second major surface of said substrate opposing said first major surface.

20. (Withdrawn) A method according to claim 12, wherein said regions of said one conductivity type are stripes.

21. (Withdrawn) A method according to claim 20, wherein said stripes extend to a depth of five microns.

22. (Withdrawn) A method according to claim 12, wherein said regions of said one conductivity type are five microns deep.